

# FFSB3065B-F085

## Automotive Silicon Carbide (SiC) Schottky Diode, 650 V

### Product Overview

For complete documentation, see the data sheet.

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

#### Features

- Max Junction Temperature 175°C
- Avalanche Rated 144 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable

#### Benefits

- PPAP capable

#### Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

#### End Products

- PHEV-EV Onboard charger and DC -DC

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Family	Configuration	V <sub>RRM</sub> (V)	I <sub>F(ave)</sub> (A)	V <sub>F</sub> (Max)	I <sub>FSM</sub> (A)	I <sub>R</sub> (Max) (µA)	Package Type
FFSB3065B-F085	3.7714		Active	D2	Single	650	30	1.7	120	120	D2PAK2 (TO-263-2L)